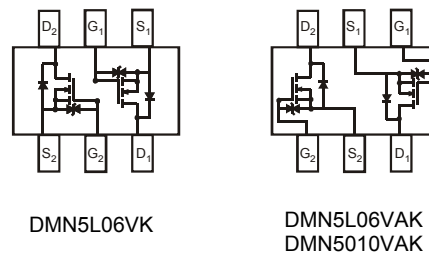


**DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**
**Features**

- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **ESD Protected up to 2kV**
- **Qualified to AEC-Q101 standards for High Reliability**

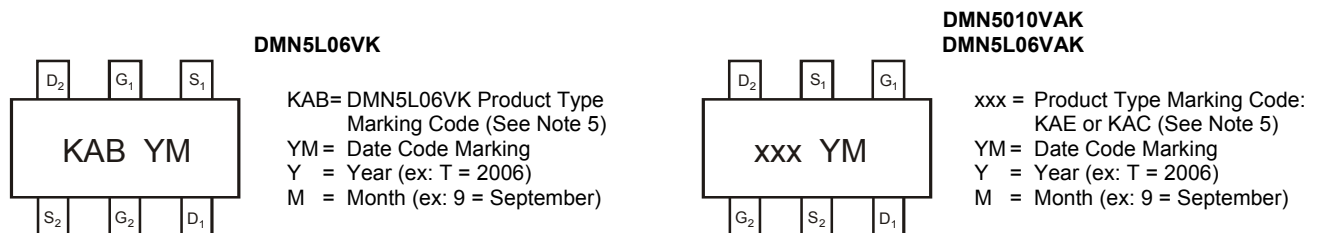
**Mechanical Data**

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)


**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN5L06VK-7	SOT563	3,000/Tape & Reel
DMN5L06VK-13	SOT563	10,000/Tape & Reel
DMN5L06VAK-7	SOT563	3,000/Tape & Reel
DMN5L06VAK-13	SOT563	10,000/Tape & Reel
DMN5010VAK-7	SOT563	3,000/Tape & Reel
DMN5010VAK-13	SOT563	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

**Marking Information** (Note 5)


## Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	T	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Note: 5. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V <sub>DSS</sub>	50	V
Drain-Gate Voltage R <sub>GS</sub> ≤ 1.0MΩ	V <sub>DGR</sub>	50	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Pulsed		±40	
Drain Current (Note 6)	I <sub>D</sub>	280	mA
	I <sub>DM</sub>	1.5	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	250	mW
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current @ T <sub>C</sub> = +25°C	I <sub>DSS</sub>	—	—	60	nA	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	1	μA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±5V, V <sub>DS</sub> = 0V
				500	nA	
				50	nA	
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage @T <sub>J</sub> = +25°C @T <sub>J</sub> = +0°C~ +85°C (Note 8)	V <sub>GS(th)</sub>	0.49 0.30	—	1.0 1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	3.0	Ω	V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 50mA V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 50mA V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 50mA
				2.5		
				2.0		
On-State Drain Current	I <sub>D(ON)</sub>	0.5	1.4	—	A	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance	Y <sub>fs</sub>	200	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	0.5	—	1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	—	50	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	5.0	pF	

- Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

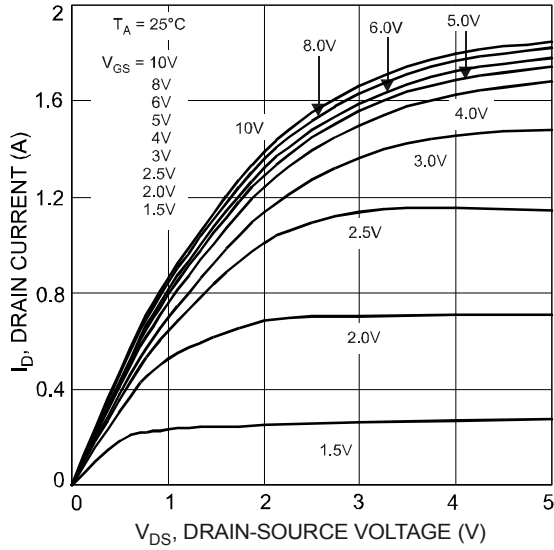


Fig. 1 Typical Output Characteristics

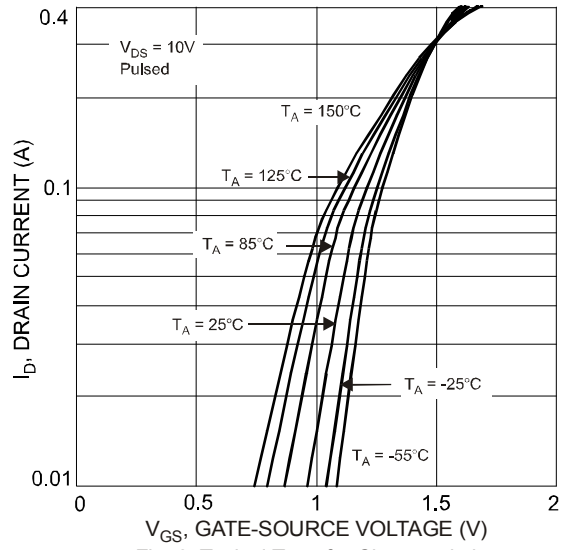


Fig. 2 Typical Transfer Characteristics

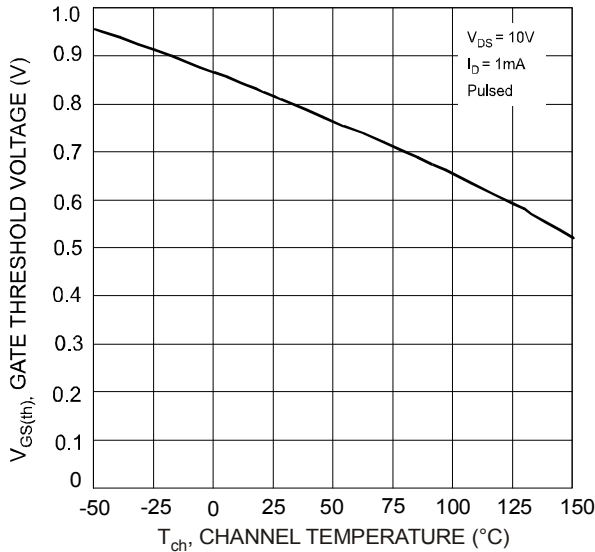


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

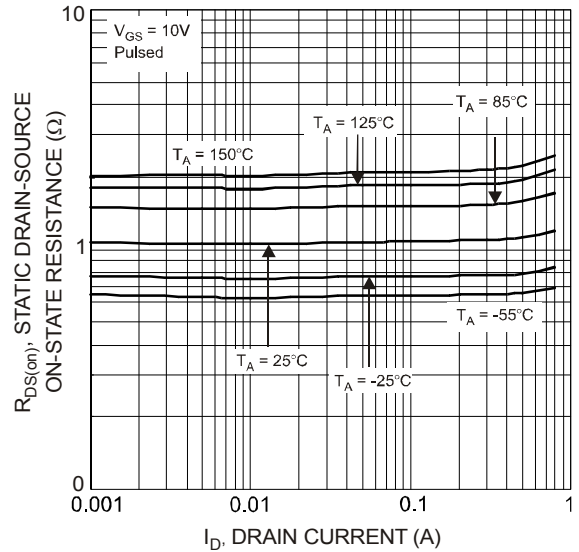


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

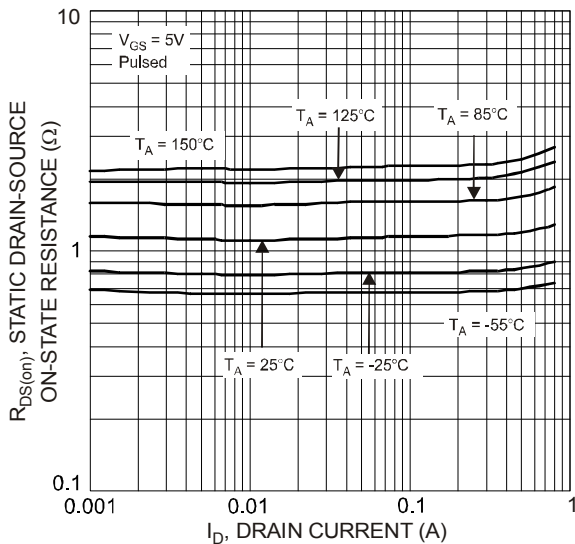


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

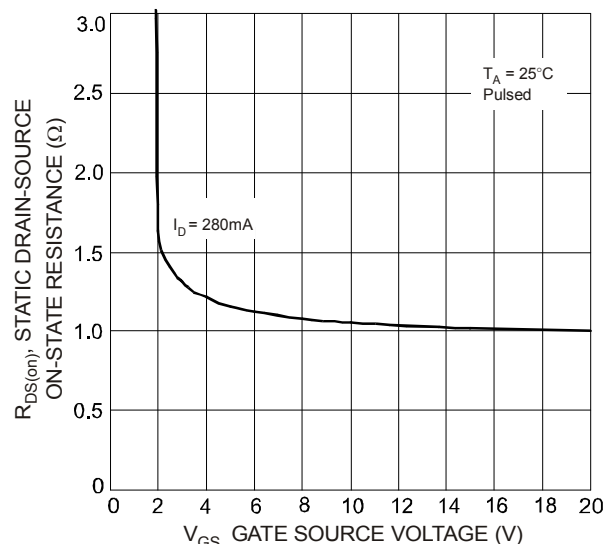


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

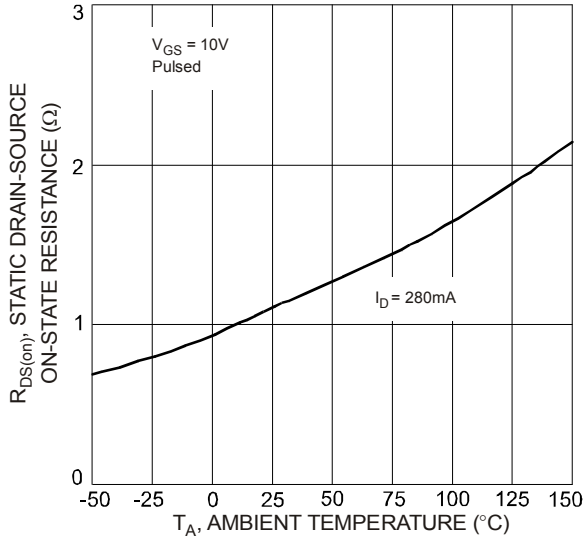


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

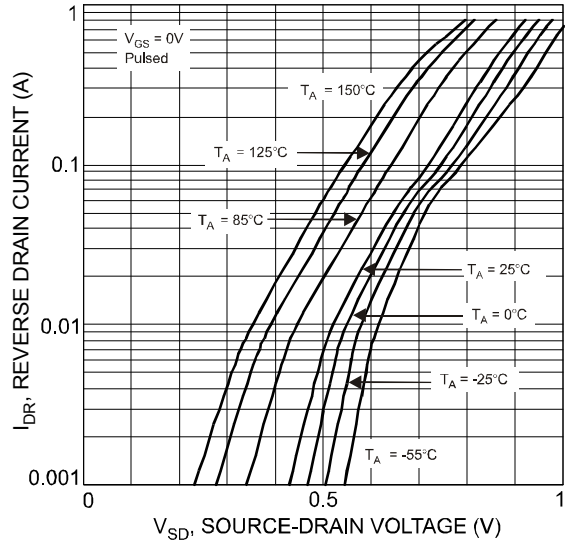


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

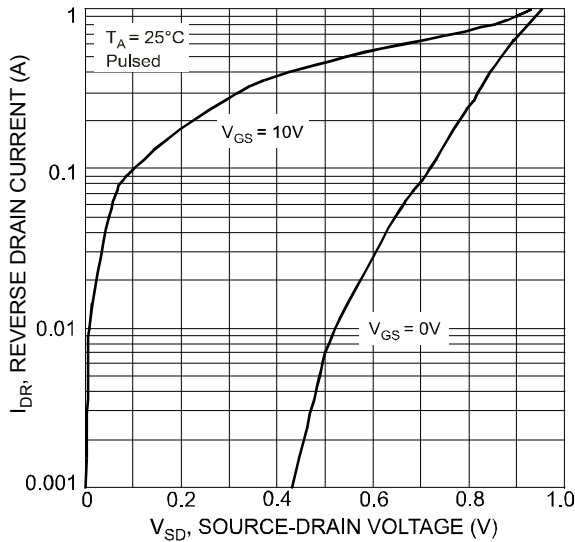


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

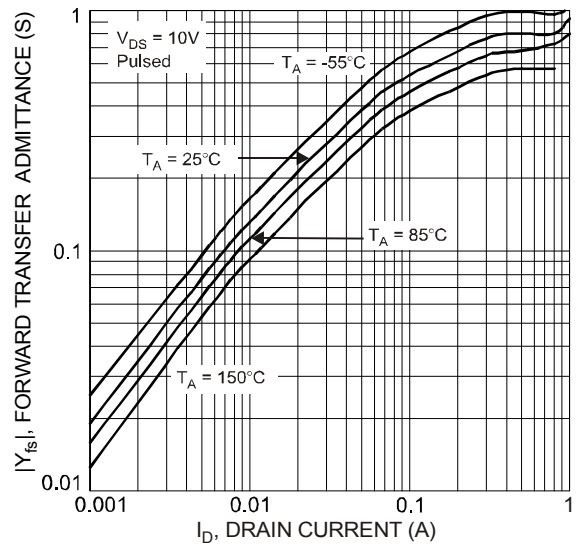


Fig. 10 Forward Transfer Admittance vs. Drain Current

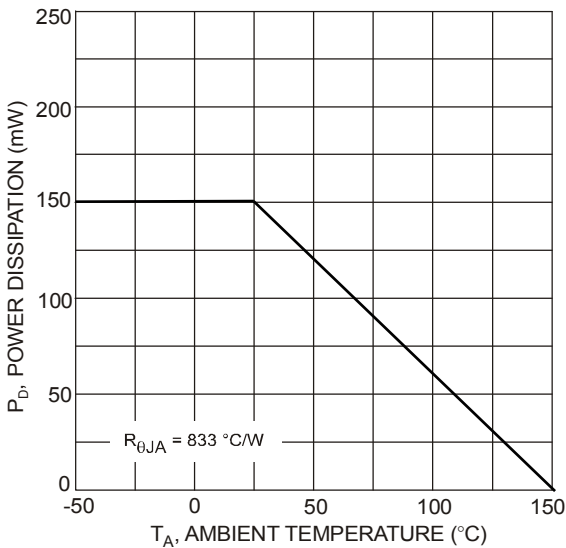
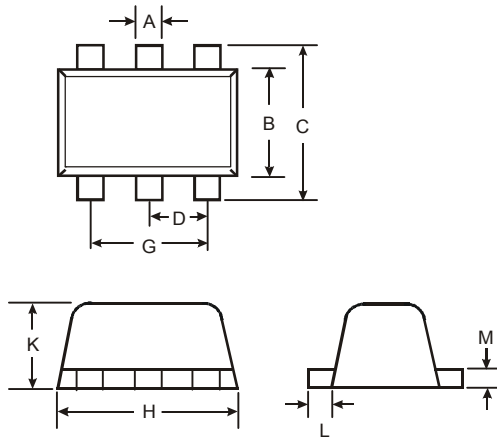


Fig. 11 Derating Curve - Total

## Package Outline Dimensions

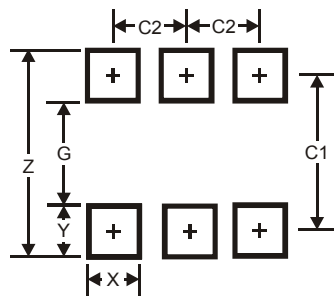
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

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